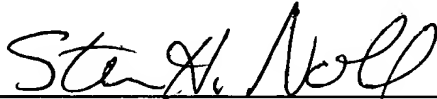


Early examination on the merits is respectfully requested.

Respectfully submitted,



(Reg. No. 28,982)

Steven H. Noll

Hill & Simpson

A Professional Corporation

85th Floor - Sears Tower

Chicago, Illinois 60606

(312) 876-0200 ext. 3899

Attorneys for Applicant(s)

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Final
Drawing
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JCS

BOX PCT

IN THE UNITED STATES DESIGNATED/ELECTED OFFICE
OF THE UNITED STATES PATENT AND TRADEMARK OFFICE
UNDER THE PATENT COOPERATION TREATY-CHAPTER II

5 **REQUEST FOR APPROVAL OF DRAWING CHANGES**

APPLICANT(S): Thomas Aeugle et al.
ATTORNEY DOCKET NO.: P99,1696
INTERNATIONAL APPLICATION NO.: PCT/EP98/01405
INTERNATIONAL FILING DATE: 11 March 1998
INVENTION: "METHOD FOR THE PRODUCTION OF A VERTICAL MOS
TRANSISTOR"

Assistant Commissioner for Patents
Washington, D.C. 20231

S I R:

Applicants herewith request approval of the drawing changes in Figures 1, 2
and 13 as shown on the drawing copies marked in red attached hereto.

Submitted by,

Steven H. Noll (Reg. 28,982)

Steven H. Noll
HILL & SIMPSON
A Professional Corporation
85th Floor - Sears Tower
Chicago, Illinois 60606
Telephone: 312/876-0200 - Ext. 3899
Attorneys for Applicant(s)

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FIG 1

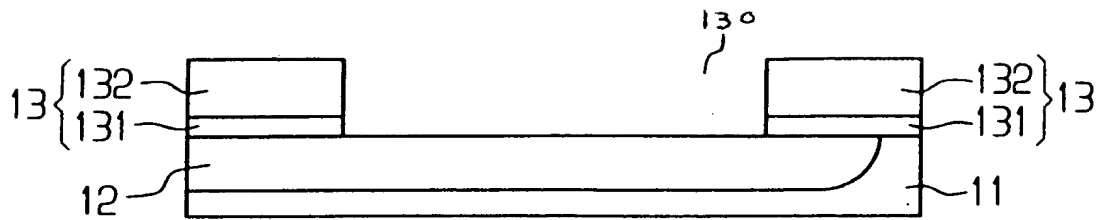


FIG 2

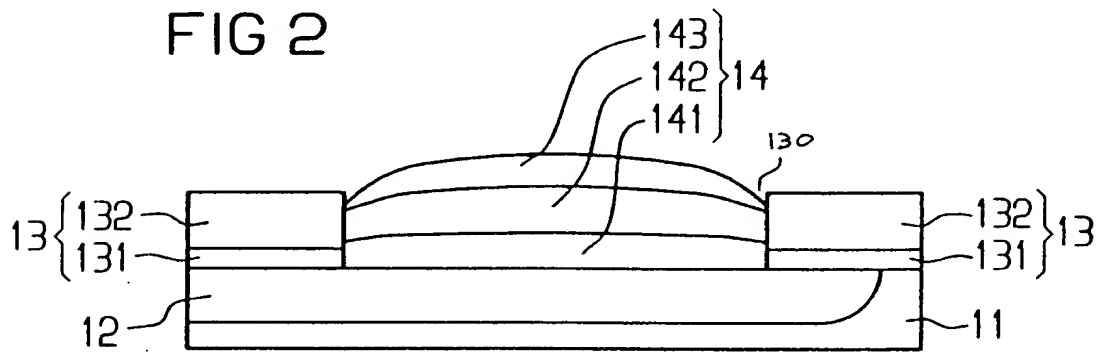
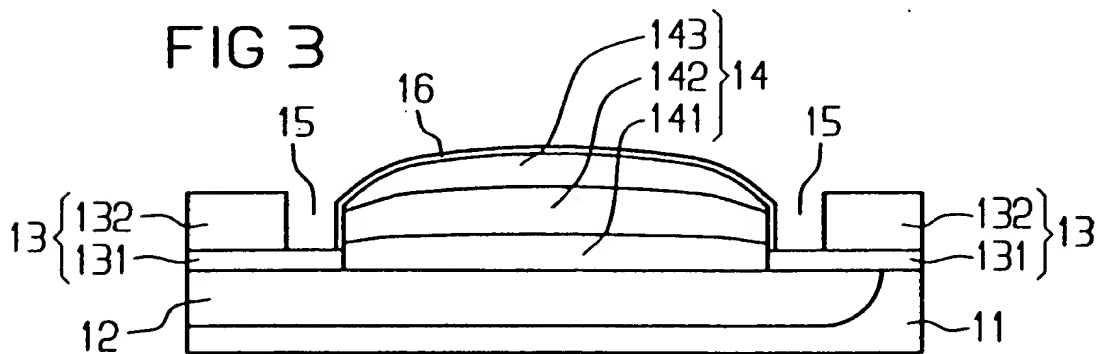


FIG 3



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FIG 13

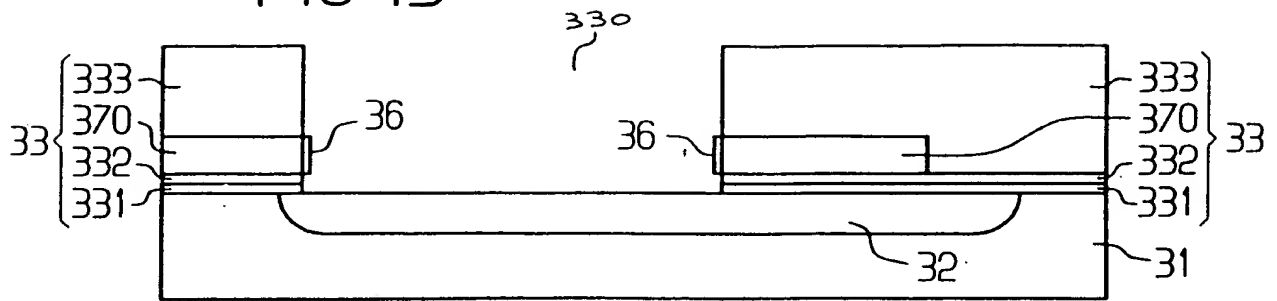


FIG 14

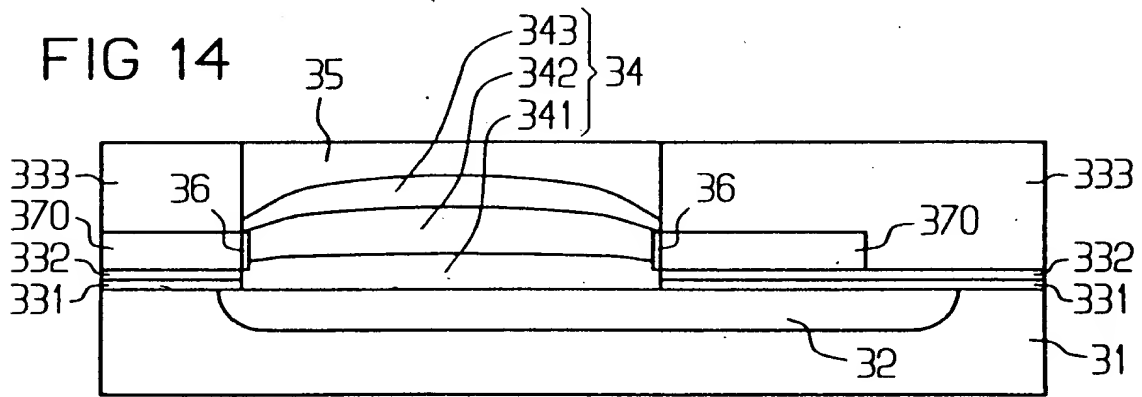
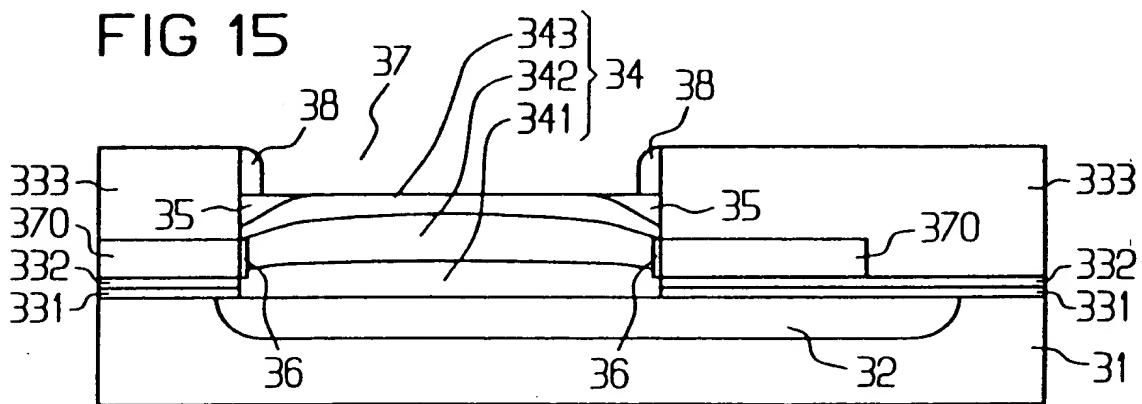


FIG 15



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